

N-Channel MOSFET Transistor

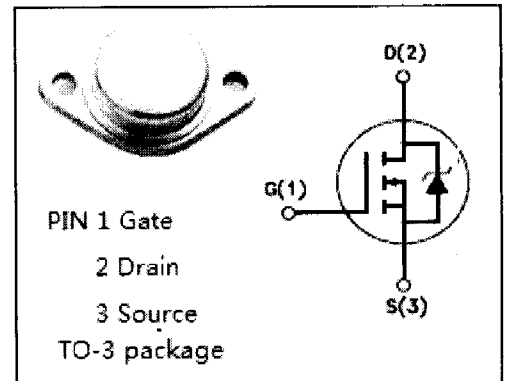
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DESCRIPTION

- silicon Gate for fast switching at elevate
- rugged

APPLICATIONS

- suited for applications such as
 Switching power supplies, motor controls, inverters,
 Choppers, audio amplifiers and high energy pulse circuits.

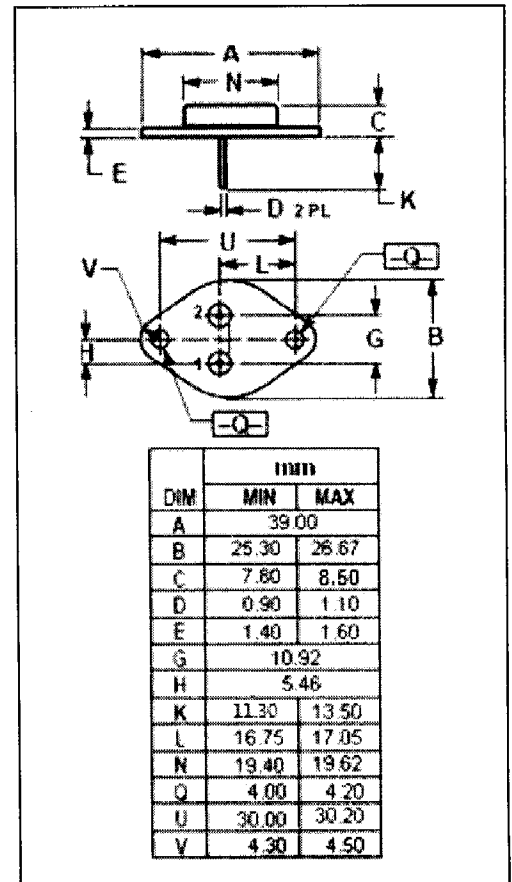


ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	400	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC=25^\circ\text{C}$	25	A
P_{tot}	Total Dissipation@ $TC=25^\circ\text{C}$	300	W
T_j	Max. Operating Junction Temperature	-55~150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Thermal Resistance, Junction to Case	0.42	$^\circ\text{C/W}$
$R_{th(j-a)}$	Thermal Resistance, Junction to Ambient	30	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS (T_c=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D =0.25mA	400			V
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =250μA	2		4	V
R _{DS(ON)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =14A			0.2	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} =±20V; V _{DS} =0			±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =400V; V _{GS} =0			250	uA
V _{SD}	Diode Forward Voltage	I _F =25A; V _{GS} =0			1.8	V
C _{iss}	Input Capacitance	V _{DS} =25V; V _{GS} =0V; f _T =1MHz		4000		pF
C _{rss}	Reverse Transfer Capacitance			550		
C _{oss}	Output Capacitance			97		